HiPerFRED

V_{RRM} = 400 V
I_{FAV} = 2x 100 A
t_{rr} = 30 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Parallel legs

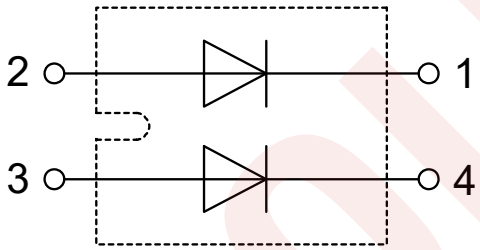
Part number

DSEP2x101-04A



Backside: isolated

E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Fast Diode

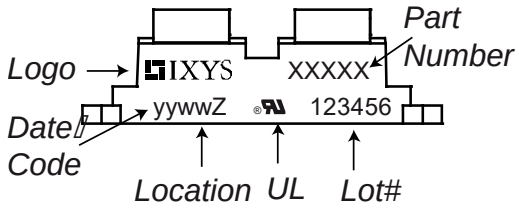
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			400	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			400	V
I_R	*reverse current, drain current*	V_R = 400 V	T_{VJ} = 25°C			1	mA
		V_R = 400 V	T_{VJ} = 150°C			4	mA
V_F	*forward voltage drop*	I_F = 100 A	T_{VJ} = 25°C			1,54	V
		I_F = 200 A				1,95	V
		I_F = 100 A	T_{VJ} = 150°C			1,22	V
		I_F = 200 A				1,73	V
I_{FAV}	*average forward current*	T_C = 45°C	T_{VJ} = 150°C			100	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0,72	V
r_F	*slope resistance* }					5	mΩ
R_{thJC}	*thermal resistance junction to case*					0,6	K/W
R_{thCH}	*thermal resistance case to heatsink*				0,1		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			200	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			1,00	kA
C_J	*junction capacitance*	V_R = 200 V f = 1 MHz	T_{VJ} = 25°C		182		pF
I_{RM}	*max. reverse recovery current*	I_F = 100 A; V_R = 200 V; -di_F/dt = 600 A/µs	T_{VJ} = 25°C		16		A
			T_{VJ} = 100°C		30		A
t_{rr}	*reverse recovery time*		T_{VJ} = 25°C		30		ns
			T_{VJ} = 100°C		85		ns

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Package SOT-227B (minibloc)					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					100	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		150	°C
Weight						30		g
M_D	*mounting torque*				1,1		1,5	Nm
M_T	*terminal torque*				1,1		1,5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	10,5	3,2			mm
$d_{Spb/Apb}$			*terminal to backside*	8,6	6,8			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		3000			V
		t = 1 minute			2500			V

Product Marking

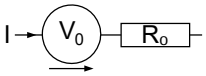


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x101-04A	DSEP2x101-04A	Tube	10	484334

Similar Part	Package	Voltage class
DPF240X400NA	SOT-227B (minibloc)	400

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 150°C

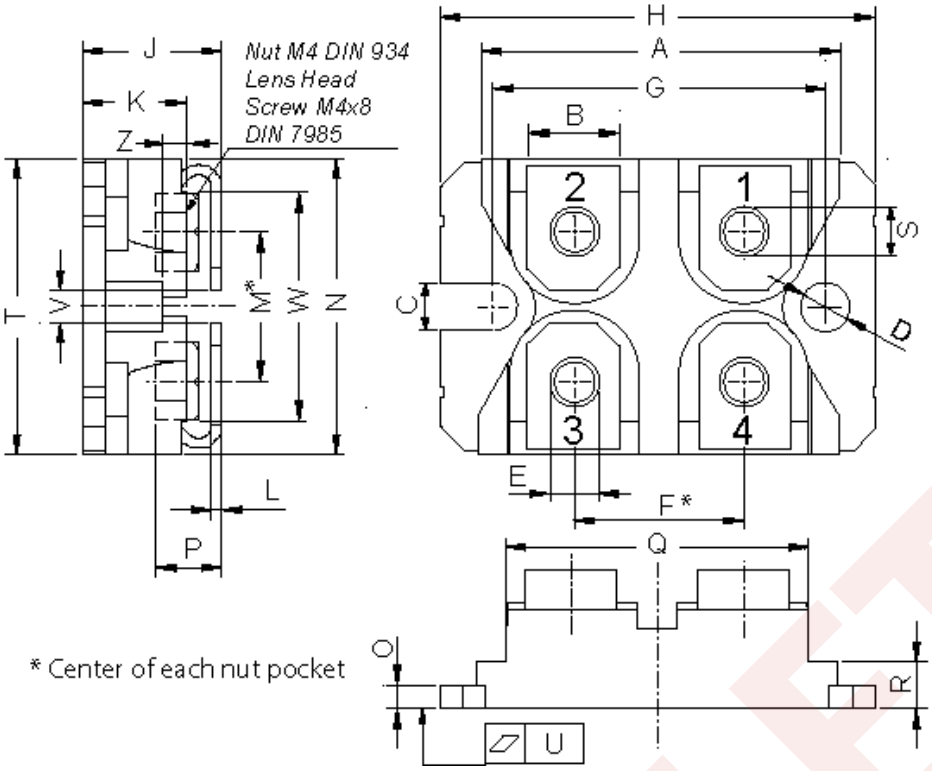


		Fast Diode	
$V_{0\,max}$	*threshold voltage*	0,72	V
$R_{0\,max}$	*slope resistance **	4,6	mΩ

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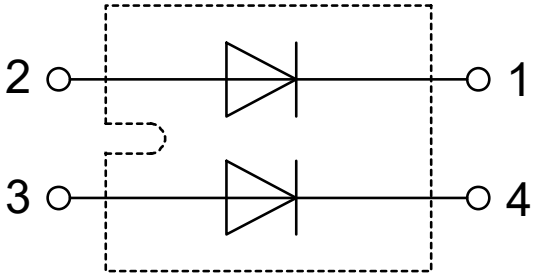
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Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

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Fast Diode

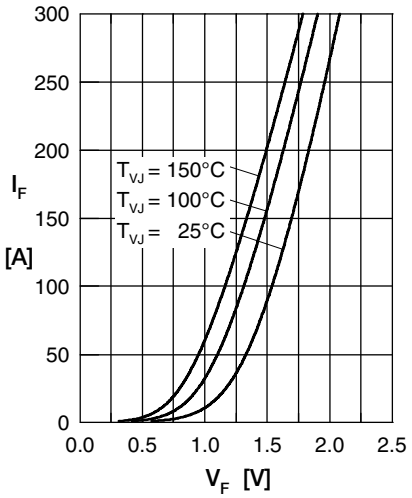


Fig. 1 Forward current I_F versus V_F

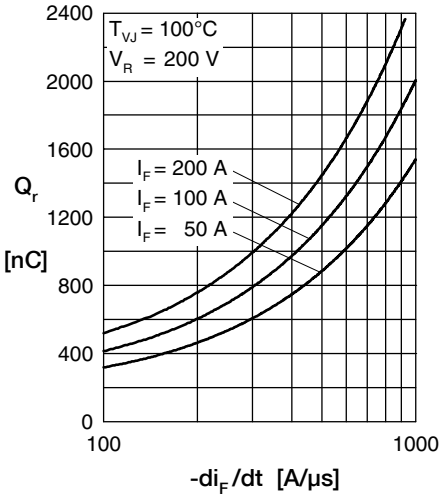


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

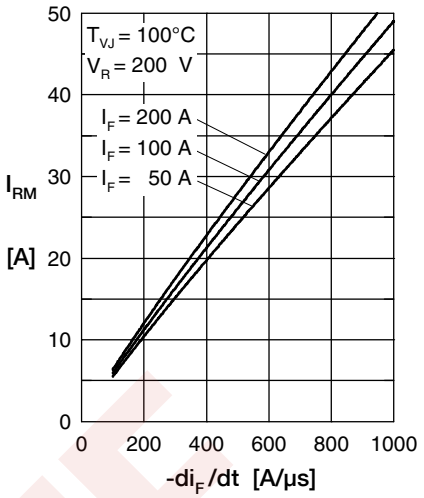


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

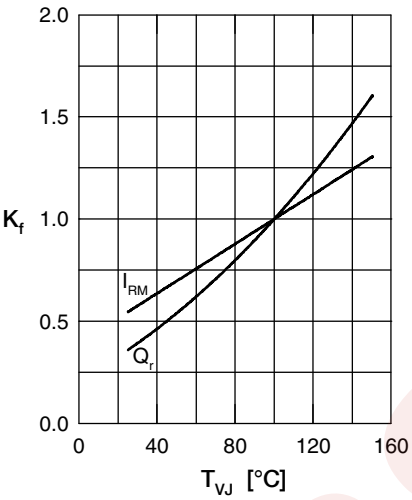


Fig. 4 Typ. dynamic parameters Q_r, I_{RM} versus T_{VJ}

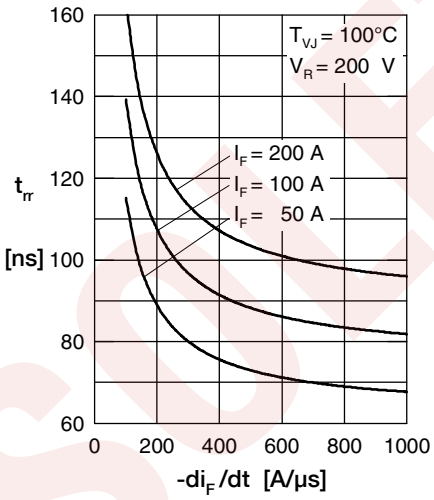


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

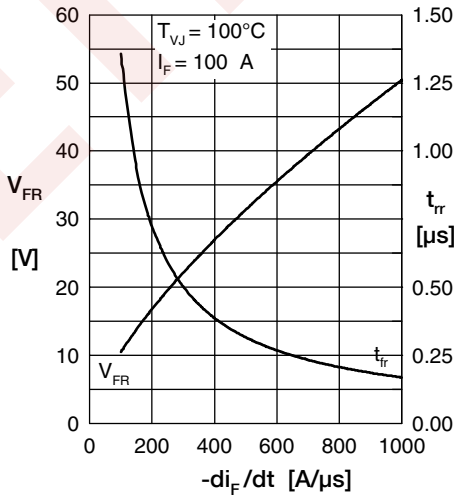


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

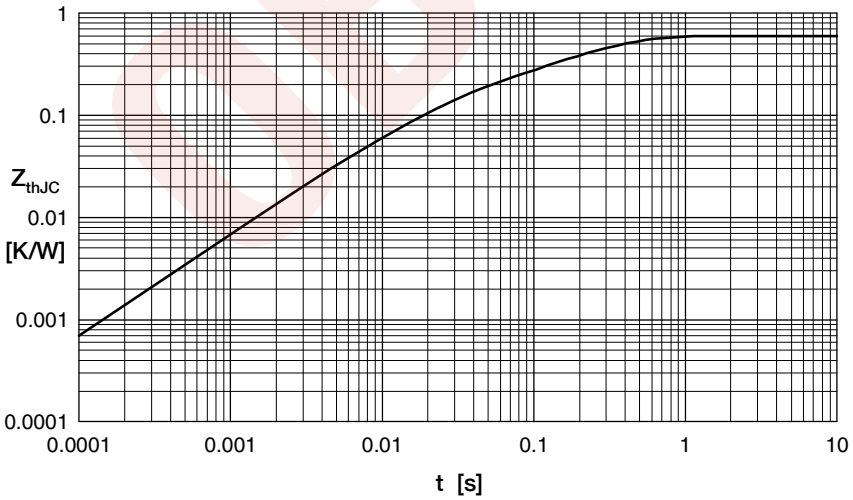


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.212	0.0055
2	0.248	0.0092
3	0.063	0.0007
4	0.077	0.0391

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